STSJ100NHS3LL

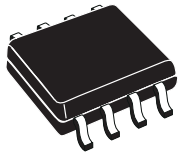
N-channel 30V - 0.0032Ω - 20A - PowerSO-8™ STripFET™III Power MOSFET plus monolithic schottky

General features

Type	V_{DSS}	$R_{DS(on)}$	I_D
STSJ100NHS3LL	30V	0.0042Ω	20A(1)

1. This value is rated accordingly to Rthj-pcb

- Optimal $R_{DS(on)}$ x Qg trade-off @ 4.5V
- Reduced switching losses
- Reduced conduction losses
- Improved junction-case thermal resistance

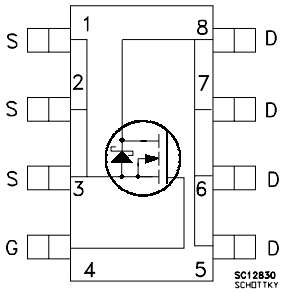


PowerSO-8

Description

This product utilizes the latest advanced design rules of ST's proprietary STripFET™ technology and a proprietary process for integrating a monolithic scottky diode. The new Power MOSFET is optimized for the most demanding synchronous switch function in DC-DC converter for Computer and Telecom.

Internal schematic diagram



Applications

- Switching application

Order codes

Part number	Marking	Package	Packaging
STSJ100NHS3LL	100HS3L-	PowerSO-8	Tape & reel

Contents

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	30	V
V_{GS}	Gate-source voltage	±16	V
I_D(1)	Drain current (continuous) at T_C = 25°C	20	A
I_D (2)	Drain current (continuous) at T_C=25°C	100	A
I_D	Drain current (continuous) at T_C=100°C	12.6	A
I_{DM}(3)	Drain current (pulsed)	80	A
P_{TOT}	Total dissipation at T_C = 25°C(2) Total dissipation at T_C = 25°C(1)	70 3	W W
T_J T_{stg}	Operating junction temperature Storage temperature	-55 to 150	°C

1. This value is rated accordingly to Rthj-pcb
2. This value is rated according to Rthj-c
3. Pulse width limited by safe operating area

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thj-c}	Thermal resistance junction-case max	1.8	°C/W
$R_{thj-pcb}$(1)	Thermal resistance junction-pcb max	42	°C/W

1. When mounted on 1 inch² FR-4 board, 2oz Cu (t<10sec.)

Table 3. Avalanche data

Symbol	Parameter	Value	Unit
I_{AV}	Avalanche current, not repetitive (pulse width limited by Tjmax)	10	A
E_{AS}	Single pulse avalanche energy (starting Tj=25°C, I_D=I_{AV}, V_{DD}=24V)	1.8	J

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1mA, V_{GS}= 0	30			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = 24V			500	µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{GS} = ±16V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 1mA	1		2.5	V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS}= 10V, I_D= 10A V_{GS}= 4.5V, I_D= 10A		0.0032 0.004	0.0042 0.0057	Ω Ω
$R_{DS(on)}$	Static drain-source on resistance	V_{GS}= 10V, I_D= 10A @125°C V_{GS}= 4.5V, I_D= 10A @125°C		0.005 0.006		Ω Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g_{fs} (1)	Forward transconductance	V_{DS} =10V, I_D = 15A		44		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} =25V, f=1MHz, V_{GS}=0		4200 700 46.2		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD}= 15V, I_D = 20A V_{GS} = 4.5V, *(see Figure 13)*		27 8.5 7.2	35	nC nC nC

1. Pulsed: pulse duration=300µs, duty cycle 1.5%

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	V_{DD}=15V, I_D=10A, R_G=4.7Ω, V_{GS}=4.5V *(see Figure 12)*		16 45		ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	V_{DD}=15V, I_D=10A, R_G=4.7Ω, V_{GS}=4.5V *(see Figure 12)*		68 8		ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}(1)	Source-drain current Source-drain current (pulsed)				20 80	A A
V_{SD}(2)	Forward on voltage	I_{SD}=5A, V_{GS}=0			0.75	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD}=20A, di/dt = 100A/µs, V_{DD}=25V, Tj=150°C *(see Figure 17)*		30 30 2		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

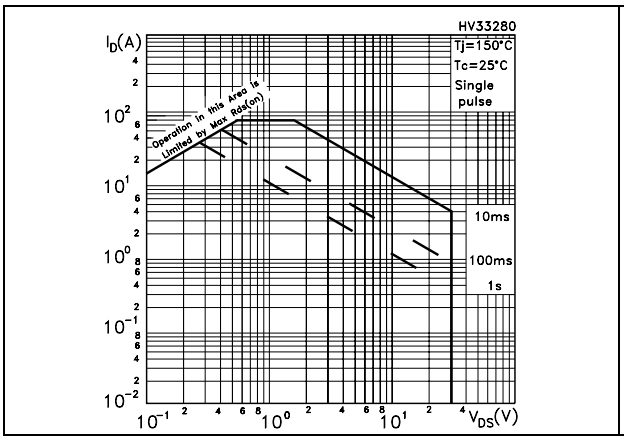


Figure 2. Thermal impedance

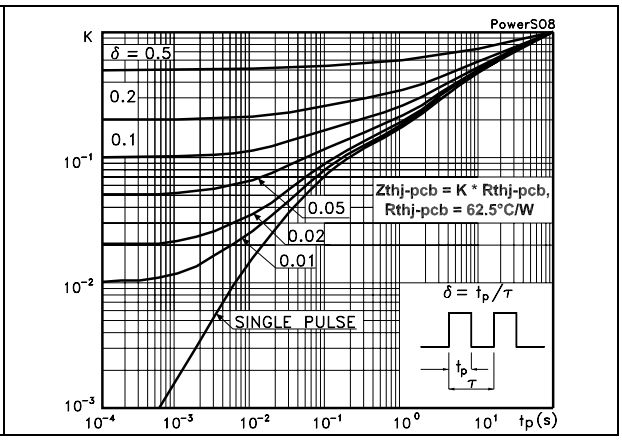


Figure 3. Output characterisics

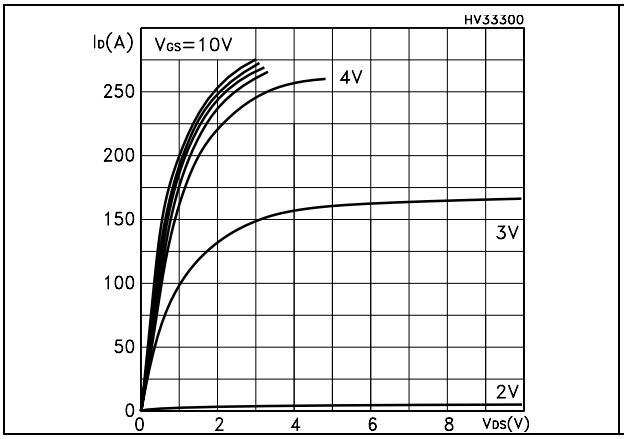


Figure 4. Transfer characteristics

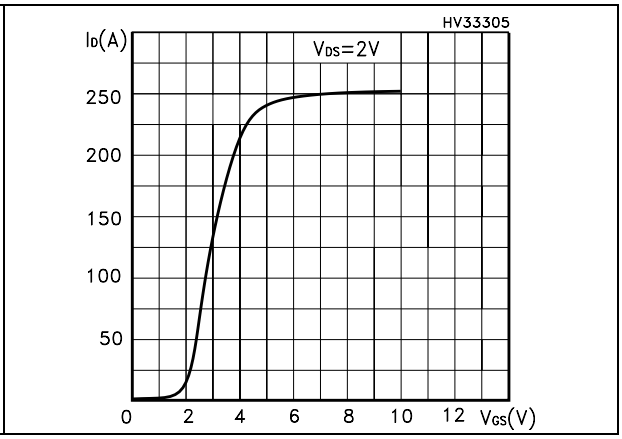


Figure 5. Normalized B_{VDSS} vs temperature

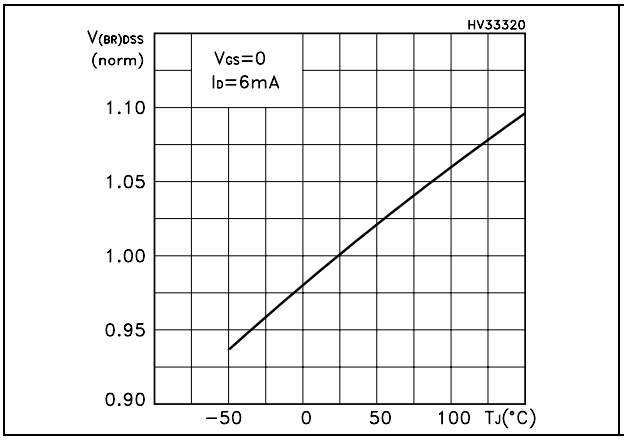


Figure 6. Static drain-source on resistance

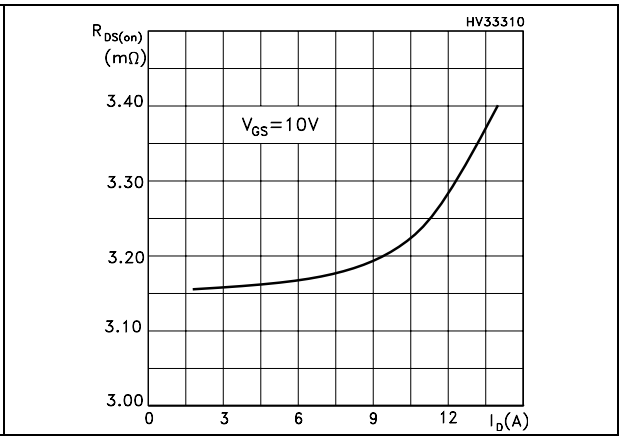


Figure 7. Gate charge vs gate-source voltage

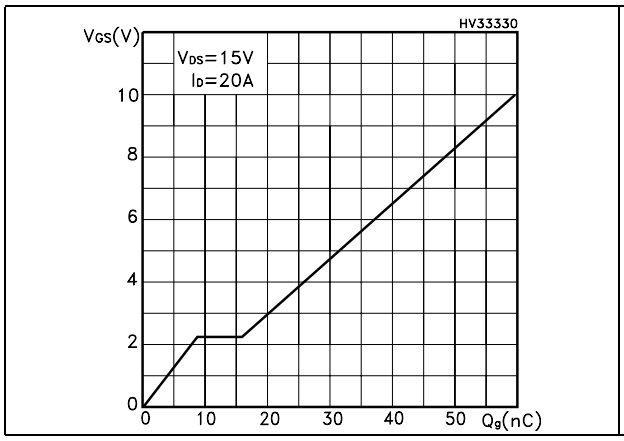


Figure 8. Capacitance variations

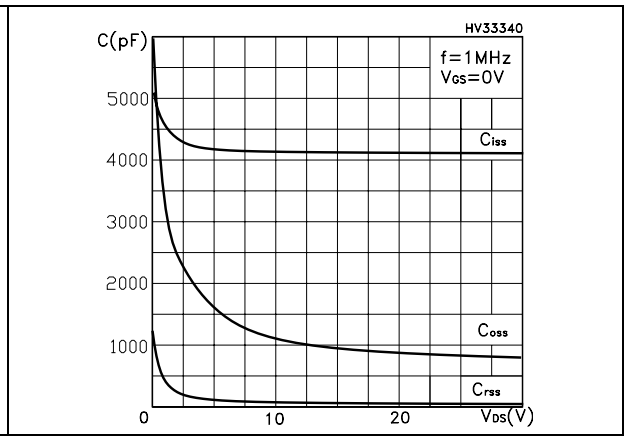


Figure 9. Normalized gate threshold voltage vs temperature

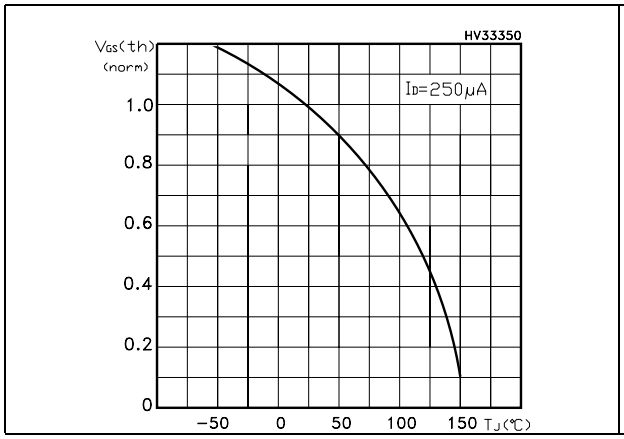


Figure 10. Normalized on resistance vs temperature

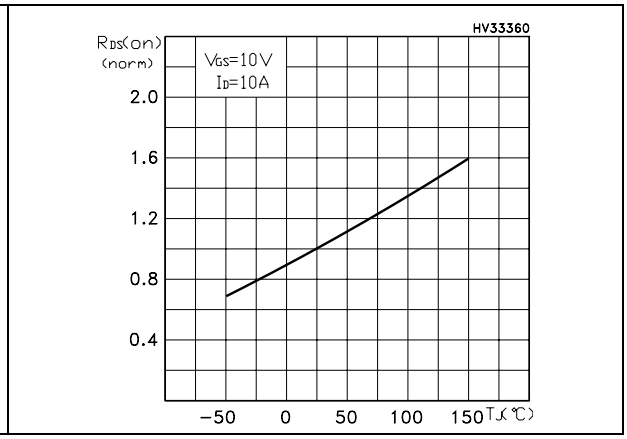
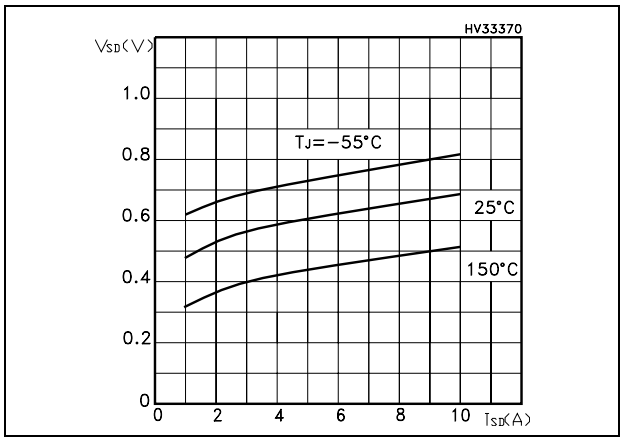


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load

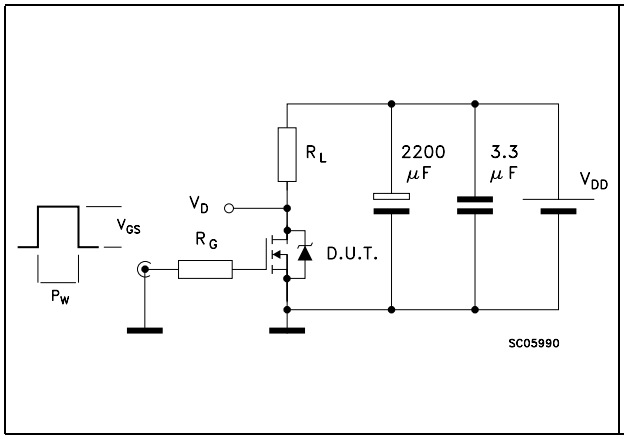


Figure 13. Gate charge test circuit

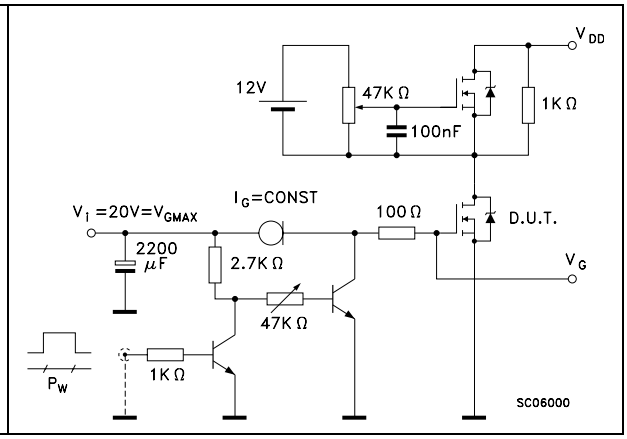


Figure 14. Test circuit for inductive load switching and diode recovery times

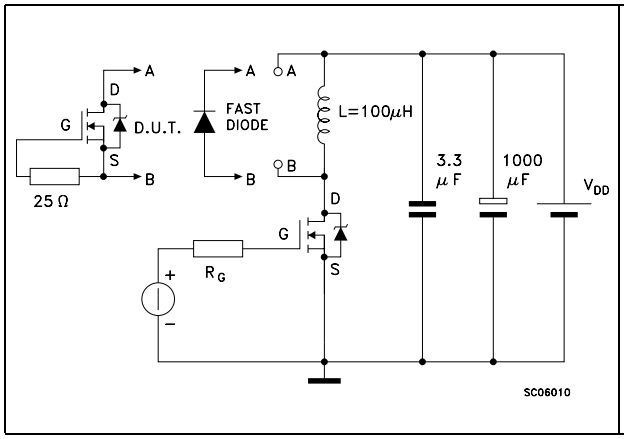


Figure 15. Unclamped inductive load test circuit

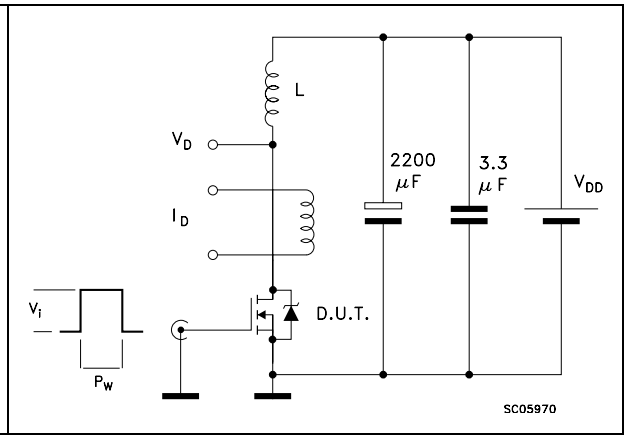


Figure 16. Unclamped inductive waveform

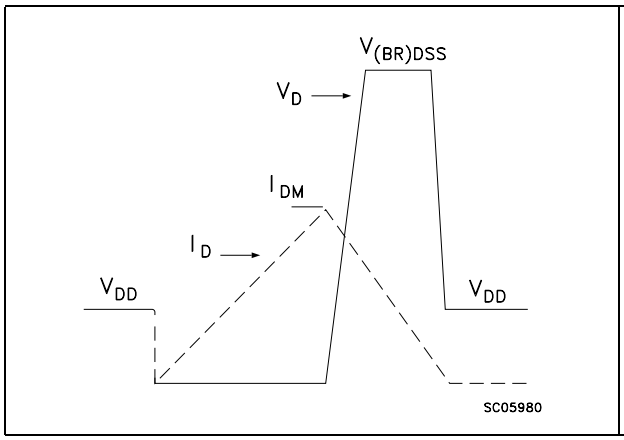
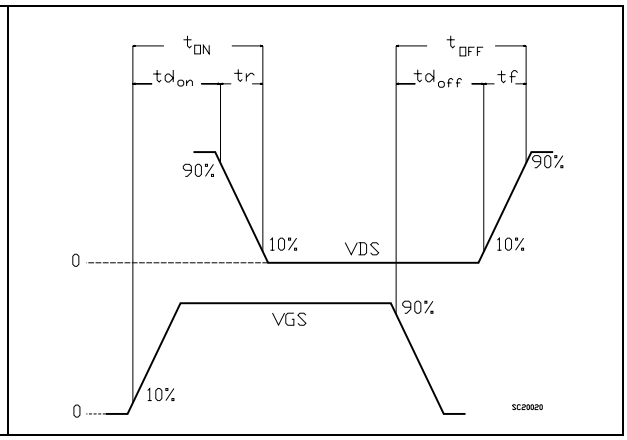


Figure 17. Switching time waveform

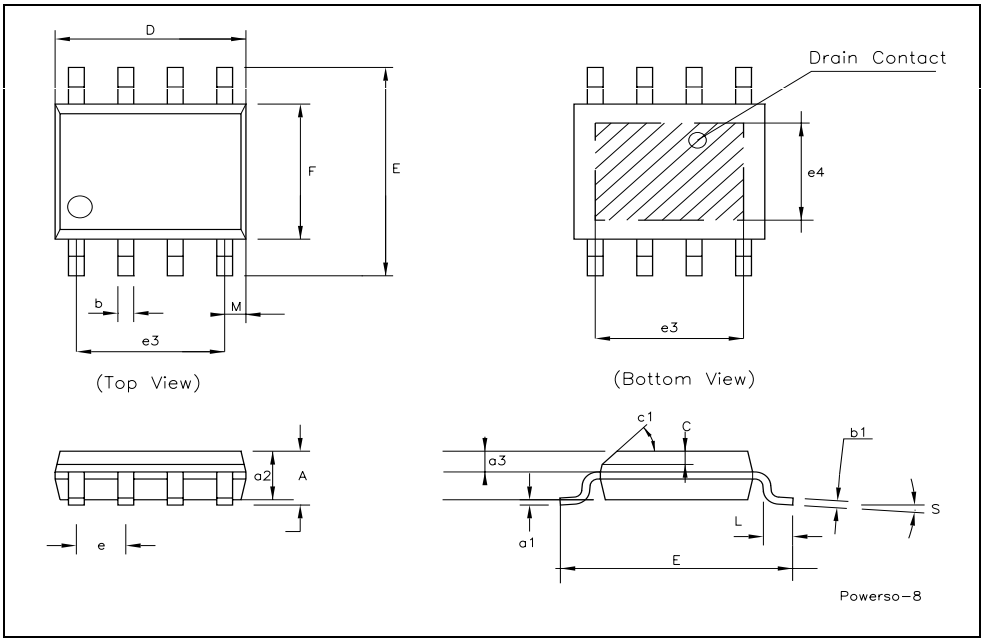


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at : *www.st.com*

PowerSO-8™ MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45° (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
e4		2.79			0.110	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8° (max.)					



5 Revision history

Table 8. Revision history

Date	Revision	Changes
13-Jan-2006	1	Initial release.
24-Jan-2006	2	Changed unit on *Table 7: Source drain diode*
18-Jul-2006	3	Complete version

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